NSN 5961-01-331-7079

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View Online at https://aerobasegroup.com/nsn/5961-01-331-7079
Inclosure Material:
Metal
Overall Length:
Between 0.160 inches and 0.180 inches
Terminal Length:
Between 0.500 inches and 0.750 inches
Overall Diameter:
Between 0.335 inches and 0.370 inches
Internal Configuration:
Field effect
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-205af
Mounting Method:
Terminal
Terminal Circle Diameter:
0.200 inches
Features Provided:
Hermetically sealed case and quality assurance level txv
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
500.0 drain to gate voltage and 500.0 drain to source voltage and 20.0 gate to source voltage
Current Rating Per Characteristic:
6.00 amperes off-state current, peak
Power Rating Per Characteristic:
20.0 watts total power dissipation
Maximum Operating Tempurature Per Measurement Point:
150.0 degrees celsius junction
Test Data Document:
81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
3 uninsulated wire lead
Specification Data:
81349-mil-prf-19500/555 government specification
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No

A110a0

Fiig:

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Mil-std (military Standard):

Mil-prf-19500 spec.